



S3ABF THRU S3MBF

Reverse Voltage - 50 to 1000 V Forward Current - 3 A

FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Lead free in comply with EU RoHS 2011/65/EU directives

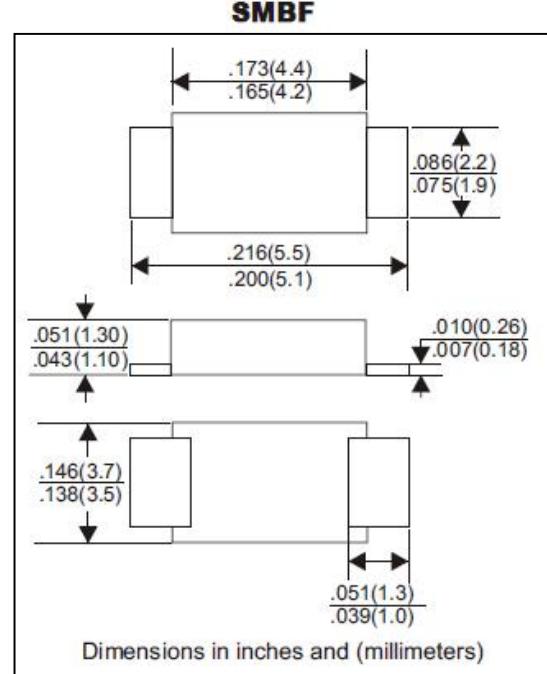
MECHANICAL DATA

- Case: SMBF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 57mg / 0.002oz

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.



Parameter	Symbols	S3ABF	S3BBF	S3DBF	S3GBF	S3JBF	S3KBF	S3MBF	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta = 65 °C	I _{F(AV)}					3			A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}					100			A
Maximum Instantaneous Forward Voltage at 3A	V _F					1.1			V
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage Ta=125 °C	I _R				5		200		μA
Typical Junction Capacitance 1)	C _j				45				pF
Typical Thermal Resistance 2)	R _{θJA}				40				°C/W
Operating and Storage Temperature Range	T _j , T _{stg}				-55 ~ +150				°C

1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

2) P.C.B. mounted with 0.5 X 0.5" (12.7 X 12.7 mm) copper pad areas.



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Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward Current Derating Curve

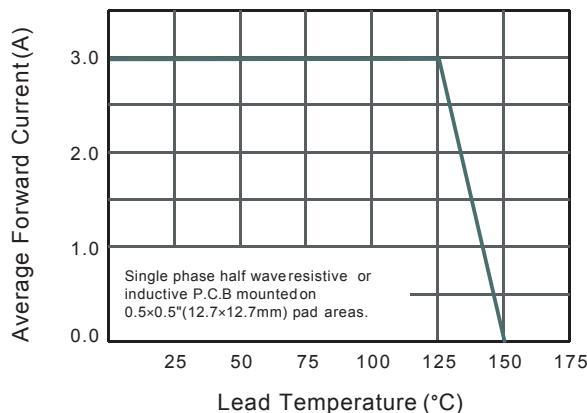


Fig.2 Typical Reverse Characteristics

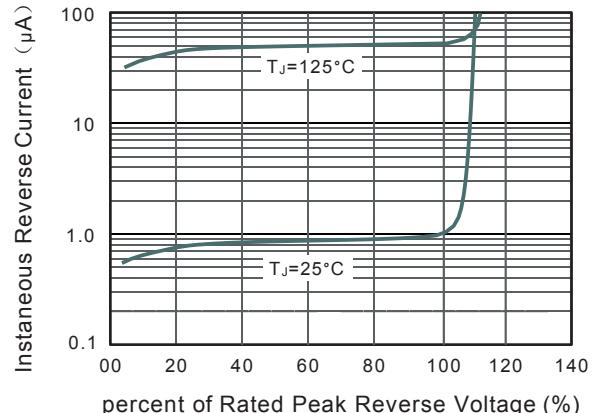


Fig.3 Typical Instantaneous Forward Characteristics

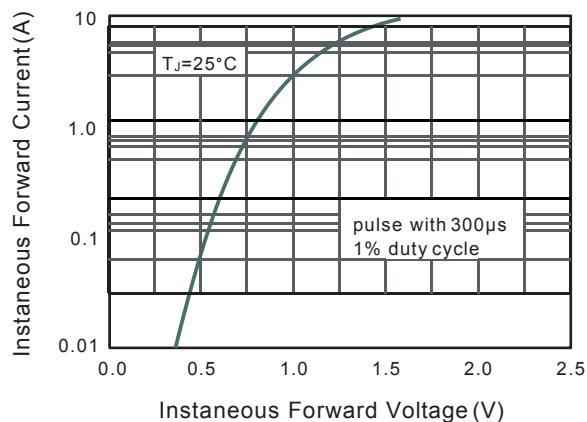


Fig.4 Typical Junction Capacitance

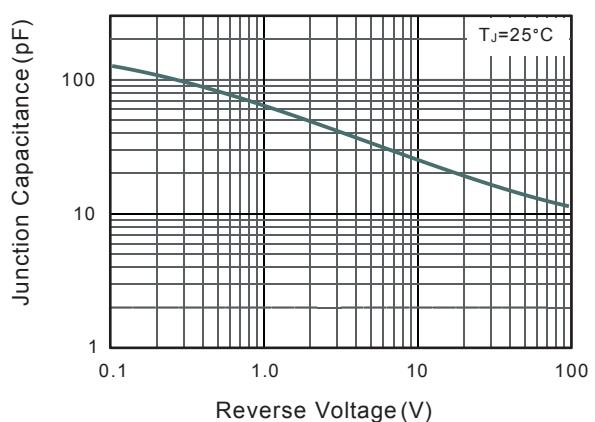


Fig.6 Maximum Non-Repetitive Peak Forward Surge Current

